ORDERING INFORMATION

Device	Temperature Range	Package
MC1445F	0°C to +75°C	Ceramic Flat
MC1445G	0°C to +75°C	Metal Can
MC1445L	0°C to +75°C	Ceramic DIP
MC1545F	−55°C to +125°C	Ceramic Flat
MC1545G	−55°C to +125°C	Metal Can
MC1545L	−55°C to +125°C	Ceramic DIP

MC1445
MC1545

GATE CONTROLLED TWO-CHANNEL-INPUT WIDEBAND AMPLIFIER

. . . designed for use as a general-purpose gated wideband-amplifier, video switch, sense amplifier, multiplexer, modulator, FSK circuit, limiter, AGC circuit, or pulse amplifier. See Application Notes AN491 for design details.

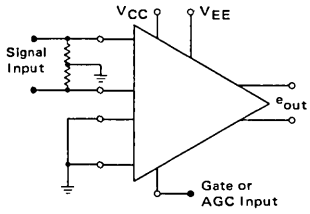
- Large Bandwidth, 50 MHz typical
- Channel-Select Time of 20 ns typical
- Differential Inputs and Differential Output

GATE CONTROLLED TWO-CHANNEL-INPUT WIDEBAND AMPLIFIER

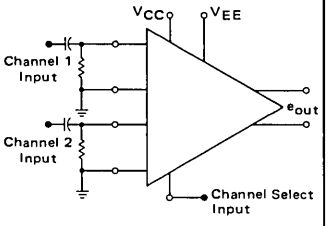
SILICON MONOLITHIC INTEGRATED CIRCUIT

TYPICAL APPLICATIONS

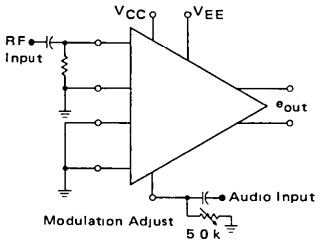
VIDEO SWITCH OR DIFFERENTIAL AMPLIFIER WITH AGC



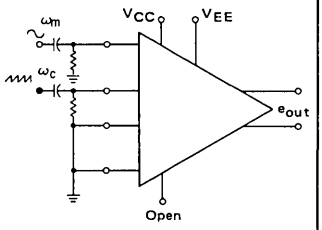
MULTIPLEX OR FSK



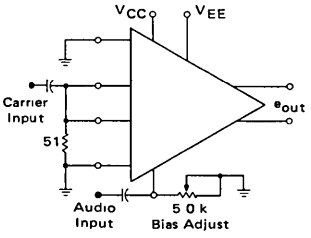
AMPLITUDE MODULATOR



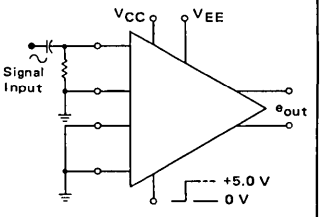
PULSE-WIDTH MODULATOR

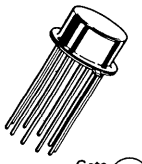


BALANCED MODULATOR

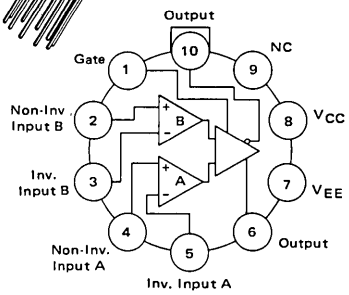


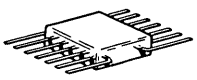
ANALOG SWITCH



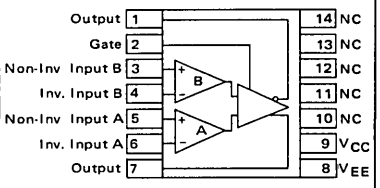


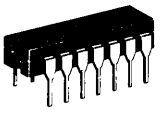
G SUFFIX
METAL PACKAGE
CASE 603
(top view)



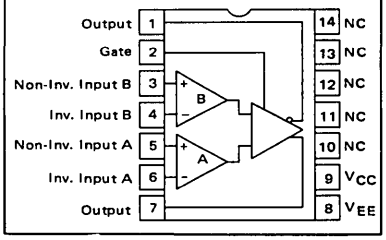


F SUFFIX
CERAMIC PACKAGE
CASE 607





L SUFFIX
CERAMIC PACKAGE
CASE 632
TO-116



6

MAXIMUM RATINGS (T_A = +25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Power Supply Voltage	V_{CC} V_{EE}	+12 -12	Vdc Vdc
Input Differential Voltage Range	V_{IDR}	±5.0	Volts
Load Current	I_L	25	mA
Power Dissipation (Package Limitation) Flat Package Derate above T_A = +25°C Ceramic Dual In-Line Package Derate above T_A = +25°C Metal Can Derate above T_A = +25°C	P_D	 500 3.3 625 5 0 680 4.6	 mW mW/°C mW mW/°C mW mW/°C
Operating Ambient Temperature Range MC1445 MC1545	T_A	0 to +75 -55 to +125	°C
Storage Temperature Range	T_{stg}	-65 to +150	°C

ELECTRICAL CHARACTERISTICS (V_{CC} = +5 0 Vdc, V_{EE} = 5 0 Vdc, at T_A = +25°C, specifications apply to both input channels unless otherwise noted)

Characteristic	Fig. No.	Symbol	MC1545 Min	MC1545 Typ	MC1545 Max	MC1445 Min	MC1445 Typ	MC1445 Max	Unit
Single-Ended Voltage Gain	1,12	A_{vs}	16	19	21	16	19 5	23	dB
Bandwidth	1,12	BW	40	50	–	–	50	–	MHz
Input Impedance (f = 50 kHz)	5,14	z_i	4 0	10	–	3 0	10	–	k ohms
Output Impedance (f = 50 kHz)	6,15	z_o	–	25	–	–	25	–	Ohms
Output Differential Voltage Range (R_L = 1 0 k ohm, f = 50 kHz)	4,13	V_{ODR}	1 5	2.5	–	1.5	2 5	–	Vp-p
Input Bias Current	16	I_{IB}	–	15	25	–	15	30	μAdc
Input Offset Current	16	I_{IO}		2 0	–	–	2 0	–	μAdc
Input Offset Voltage	17	V_{IO}	–	1 0	5.0	–	–	7.5	mVdc
Quiescent Output dc Level	17	V_O	–	0.1	–	–	0.1	–	Vdc
Output dc Level Change (Gate Input Voltage Change +5 0 V to 0 V)	17	ΔV_O	–	±15	–	–	±15	–	mV
Common-Mode Rejection Ratio (f = 50 kHz)	9,18	CMRR	–	85	–	–	85	–	dB
Input Common-Mode Voltage Range	18	V_{ICR}	–	±2 5	–	–	±2 5	–	Vp
Gate Characteristics Gate Input Voltage – Low Logic State (Note 1) Gate Input Voltage – High Logic State (Note 2)	8	$V_{IL(G)}$ $V_{IH(G)}$	0.40 –	0.70 1.5	– 2.2	0 2 –	0.4 1 3	– 3 0	Vdc
Gate Input Current – Low Logic State ($V_{IL(G)}$ = 0 V)	18	$I_{IL(G)}$	–	–	2 5	–	–	4.0	mA
Gate Input Current – High Logic State ($V_{IH(G)}$ = +5.0 V)	18	$I_{IH(G)}$	–	–	2.0	–	–	4 0	μA
Step Response (e_{in} = 20 mV)	19	t_{PLH} t_{PHL} t_{TLH} t_{THL}	– – – –	6 5 6.3 6.5 7.0	10 10 15 15	– – – –	6.5 6 3 6 5 7 0	– – – –	ns
Wideband Input Noise (5.0 Hz – 10 MHz, R_S = 50 ohms)	10,20	e_n	–	25	–	–	25	–	μV(rms)
DC Power Consumption	11,20	P_C	–	70	110	–	70	150	mW

Note 1. $V_{IL(G)}$ is the gate voltage which results in channel A gain of unity or less and channel B gain of 16 dB or greater.
Note 2. $V_{IH(G)}$ is the gate voltage which results in channel B gain of unity or less and channel A gain of 16 dB or greater.

FIGURE 1 – SINGLE-ENDED VOLTAGE GAIN versus FREQUENCY

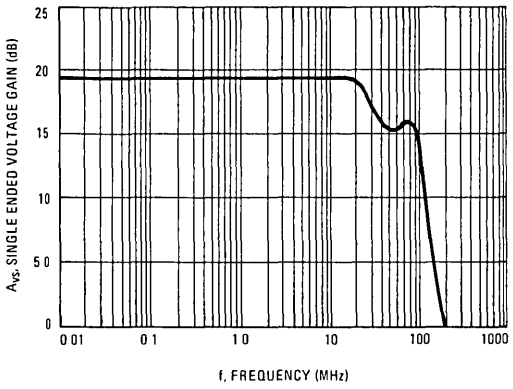


FIGURE 2 – SINGLE-ENDED VOLTAGE GAIN versus TEMPERATURE

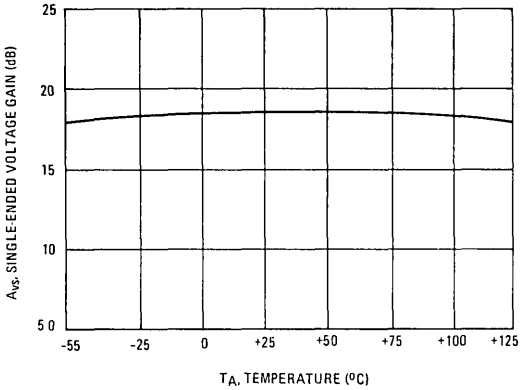


FIGURE 3 – VOLTAGE GAIN versus POWER SUPPLY VOLTAGES

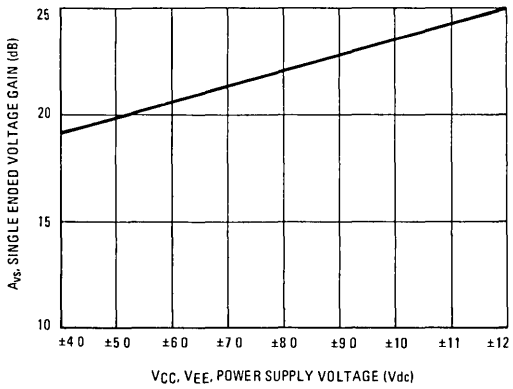


FIGURE 4 – OUTPUT VOLTAGE SWING versus LOAD RESISTANCE

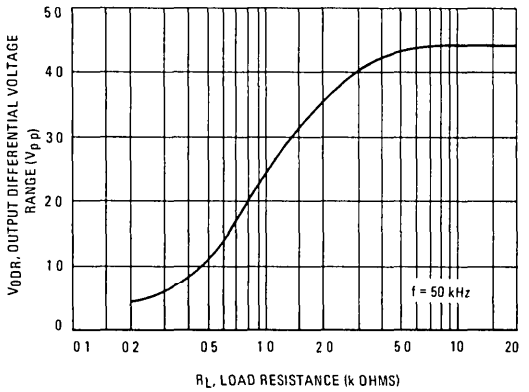


FIGURE 5 – INPUT Cp AND Rp versus FREQUENCY (BOTH CHANNELS)

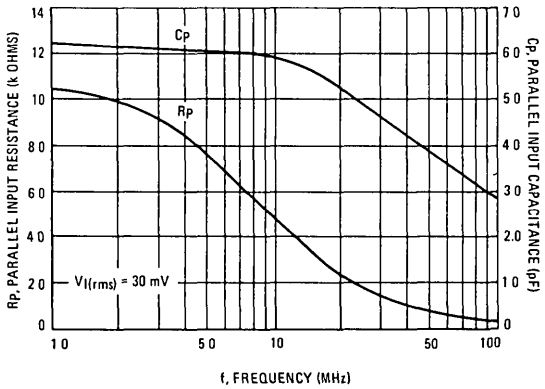


FIGURE 6 – OUTPUT IMPEDANCE versus FREQUENCY

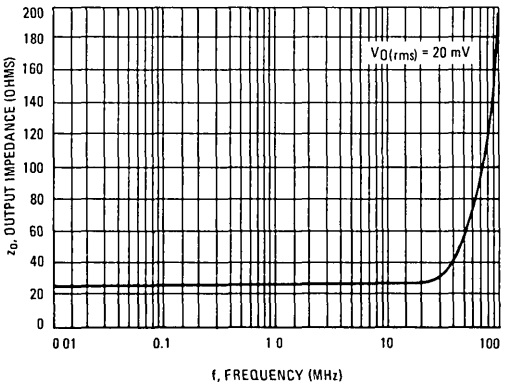


FIGURE 7 – CHANNEL SEPARATION versus FREQUENCY

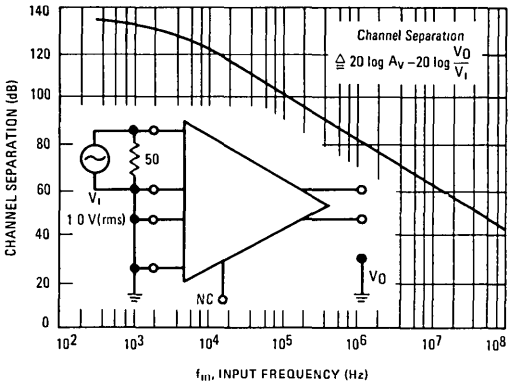


FIGURE 8 – GATE CHARACTERISTICS

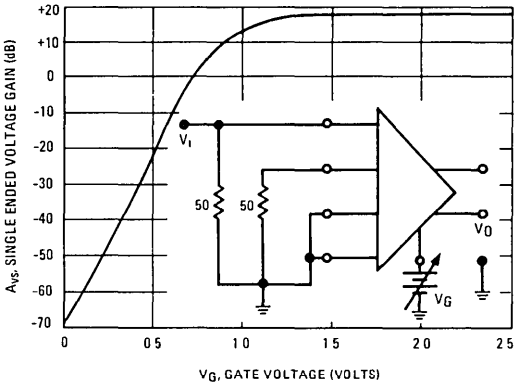


FIGURE 9 – COMMON MODE REJECTION RATIO versus FREQUENCY

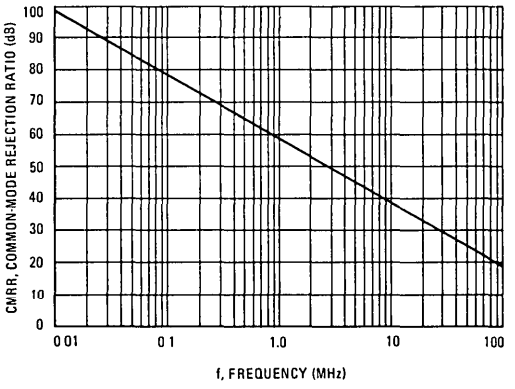


FIGURE 10 – INPUT WIDEBAND NOISE versus SOURCE RESISTANCE

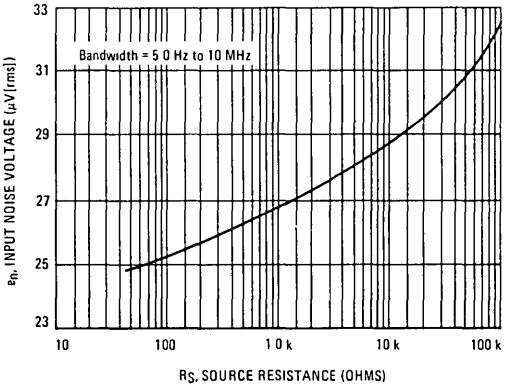


FIGURE 11 – CIRCUIT SCHEMATIC

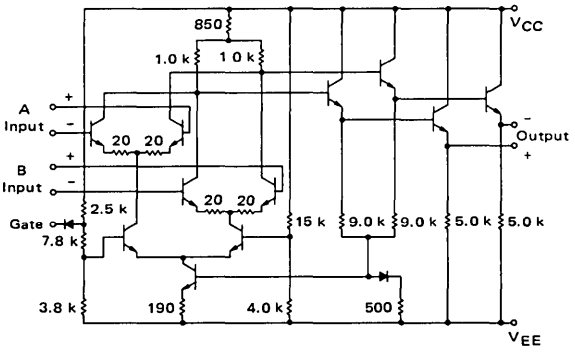


FIGURE 12 – SINGLE-ENDED VOLTAGE GAIN AND BANDWIDTH TEST CIRCUIT

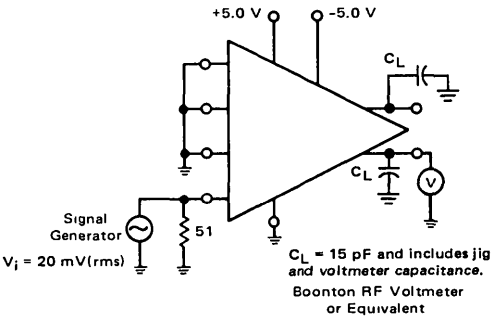


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FIGURE 13 – OUTPUT VOLTAGE SWING TEST CIRCUIT

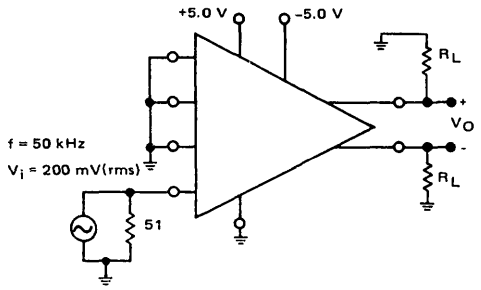


FIGURE 14 – INPUT IMPEDANCE TEST CIRCUIT

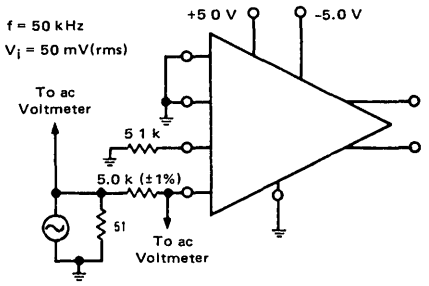


FIGURE 15 – OUTPUT IMPEDANCE TEST CIRCUIT

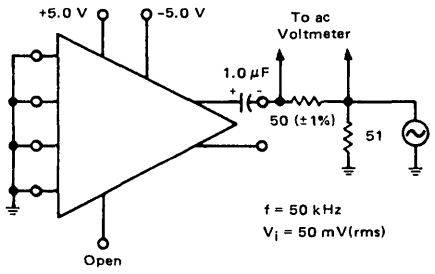


FIGURE 16 – INPUT BIAS CURRENT AND INPUT OFFSET CURRENT TEST CIRCUIT

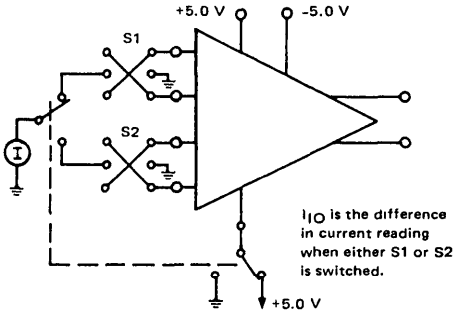


FIGURE 17 – INPUT OFFSET VOLTAGE AND QUIESCENT OUTPUT LEVEL TEST CIRCUIT

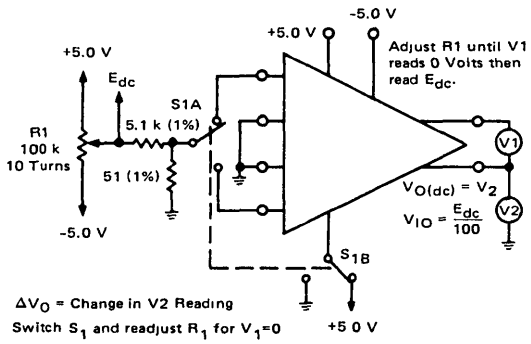


FIGURE 18 – GATE CURRENT (HIGH AND LOW), COMMON-MODE REJECTION AND COMMON-MODE INPUT RANGE TEST CIRCUIT

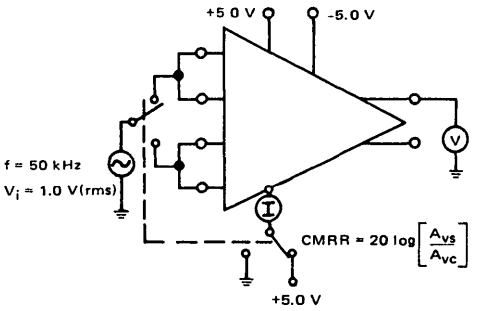
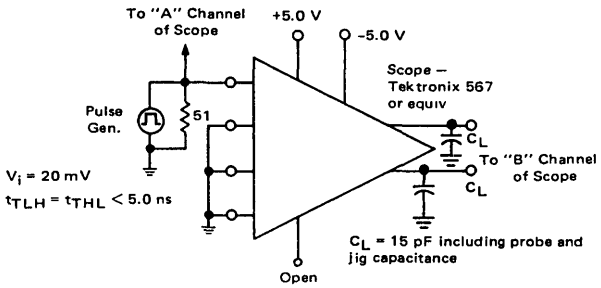


FIGURE 19 – PROPAGATION DELAY AND RISE AND FALL TIMES TEST CIRCUIT



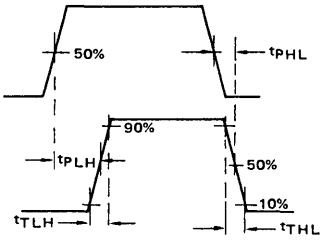


FIGURE 20 – POWER DISSIPATION AND WIDEBAND INPUT NOISE TEST CIRCUIT

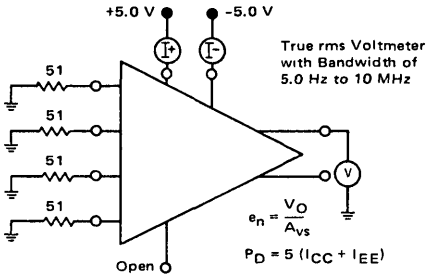
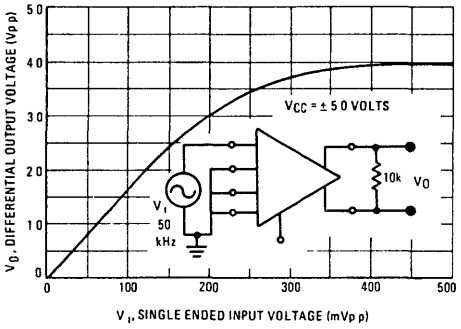


FIGURE 21 – LIMITING CHARACTERISTIC



6